

Device characteristics

EE3002: Analog Circuits

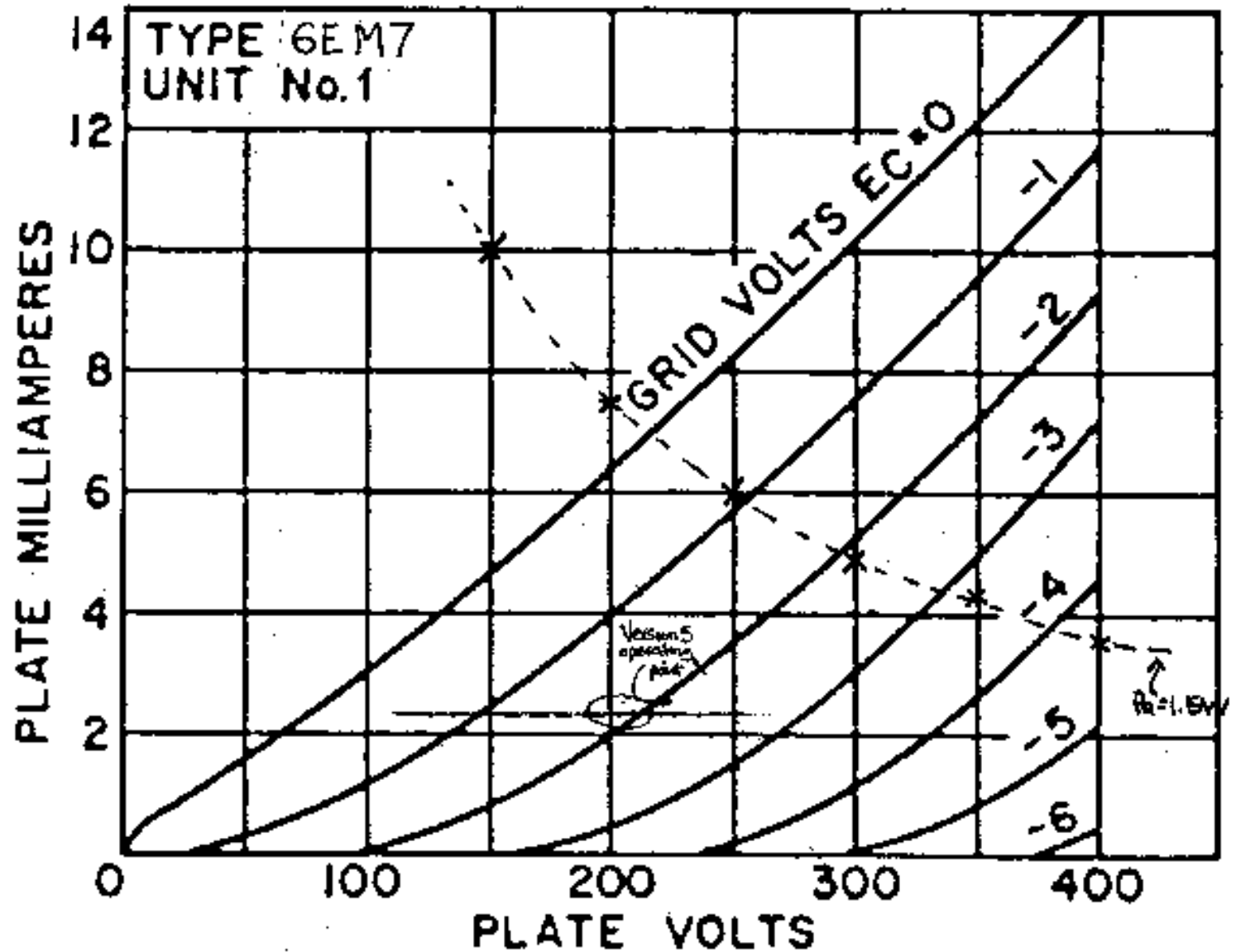
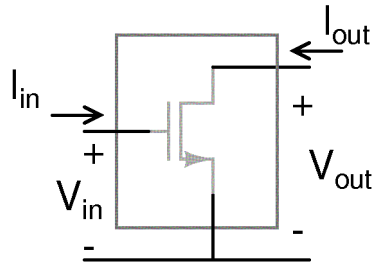
EE5310: Analog Electronic Circuits

Nagendra Krishnapura

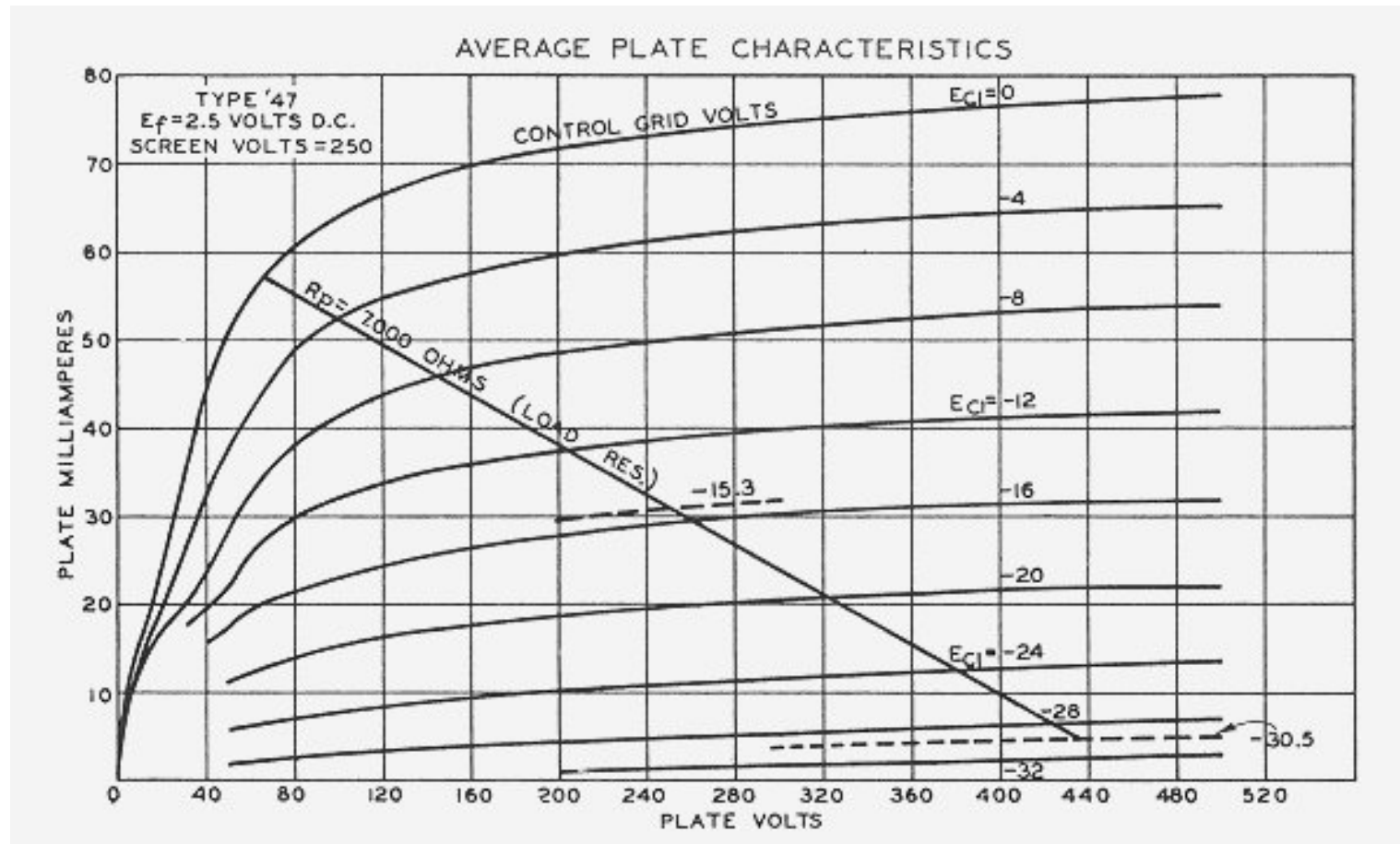
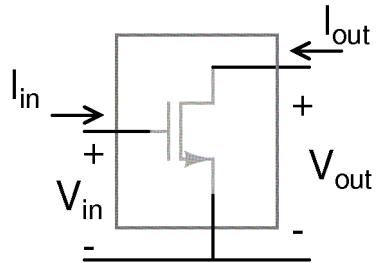
Dept. of EE

IIT Madras

Triode: I_{out} vs. V_{out}

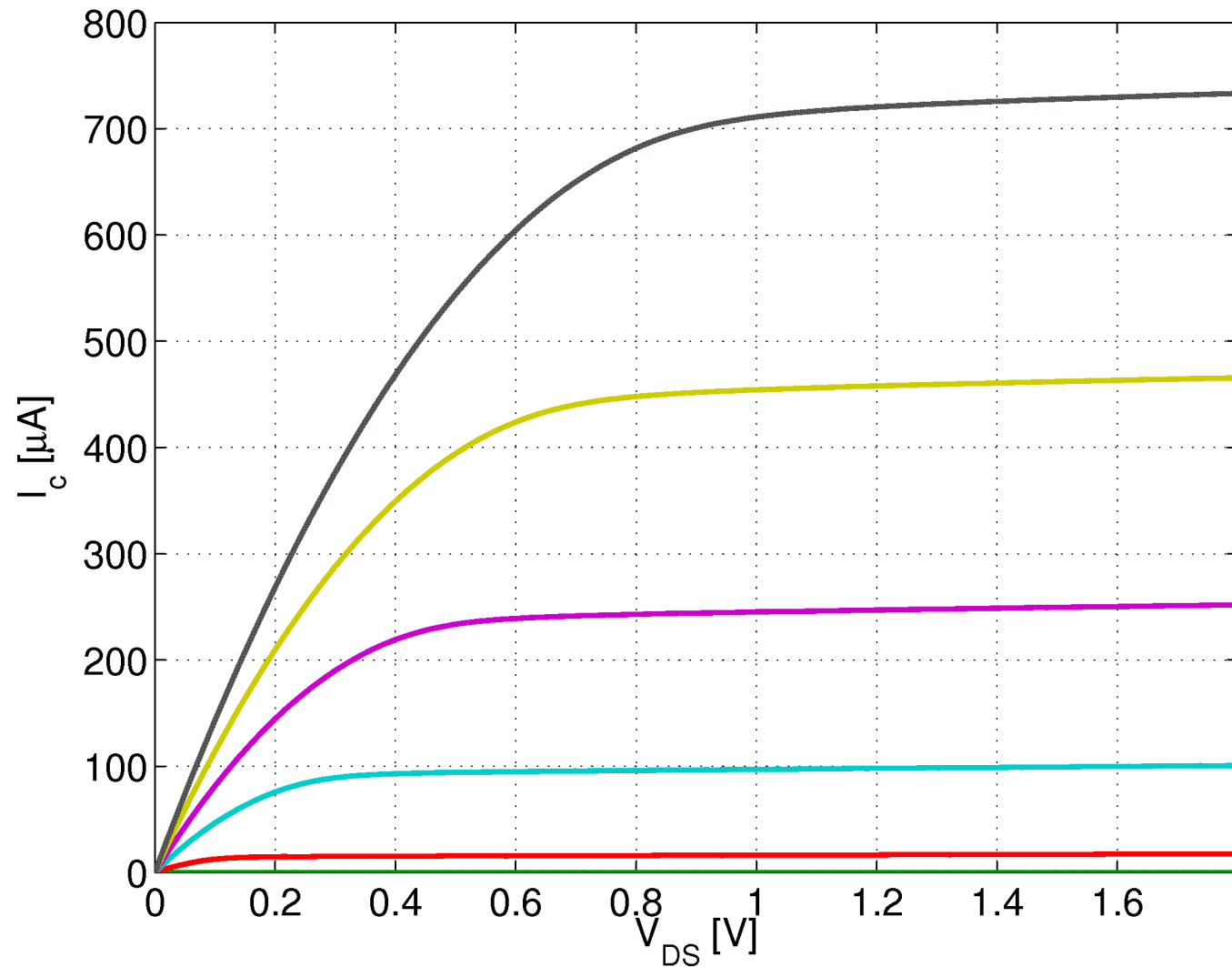
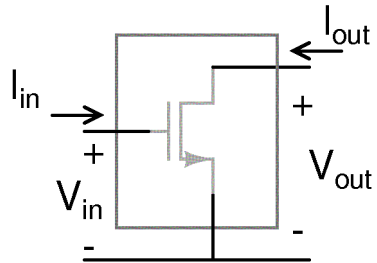


Pentode: I_{out} vs. V_{out}

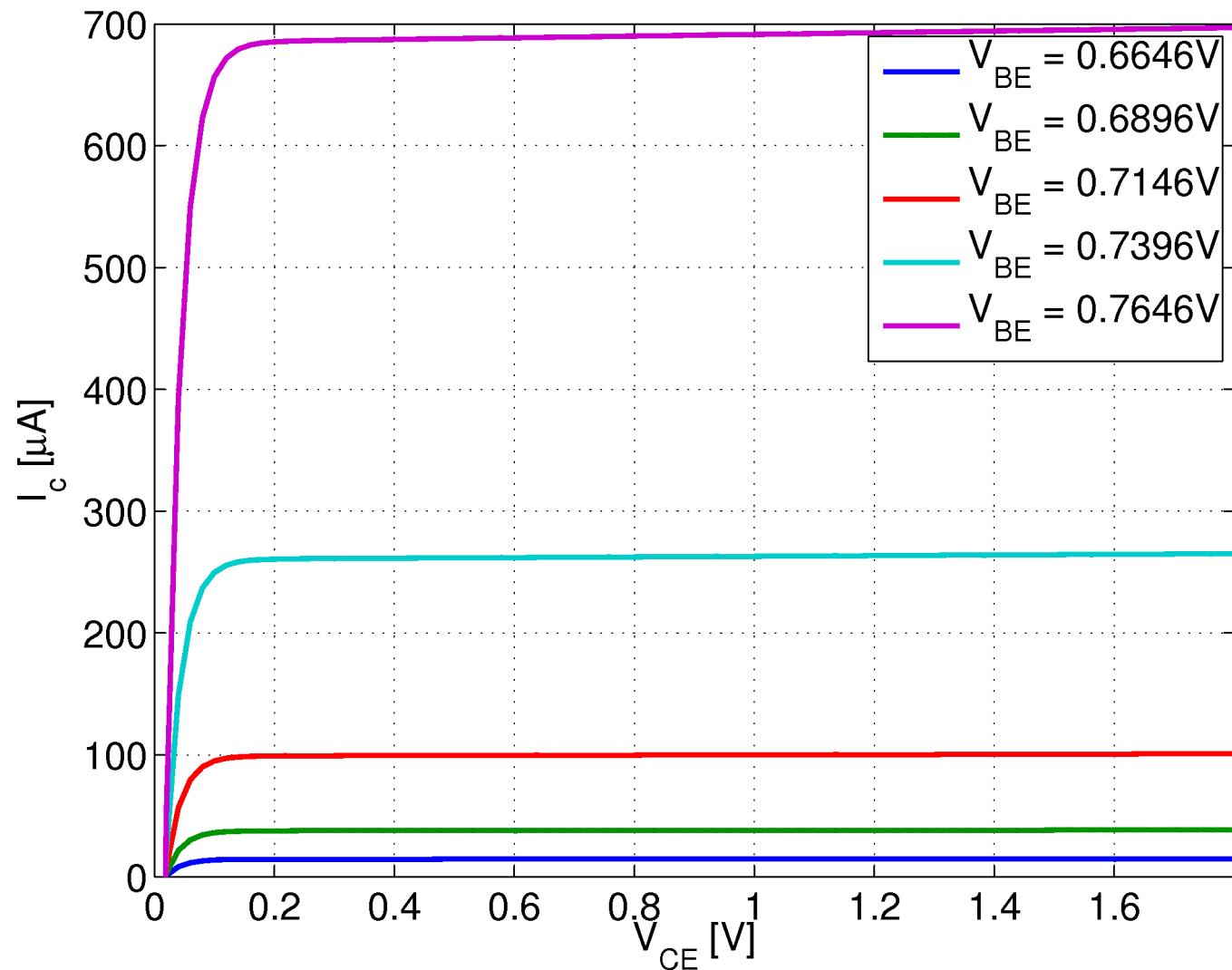
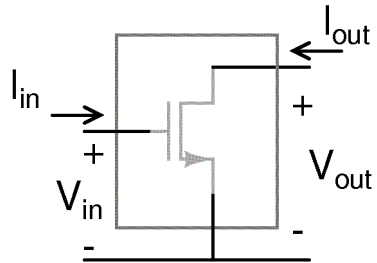


nMOS: I_{out} vs. V_{out}

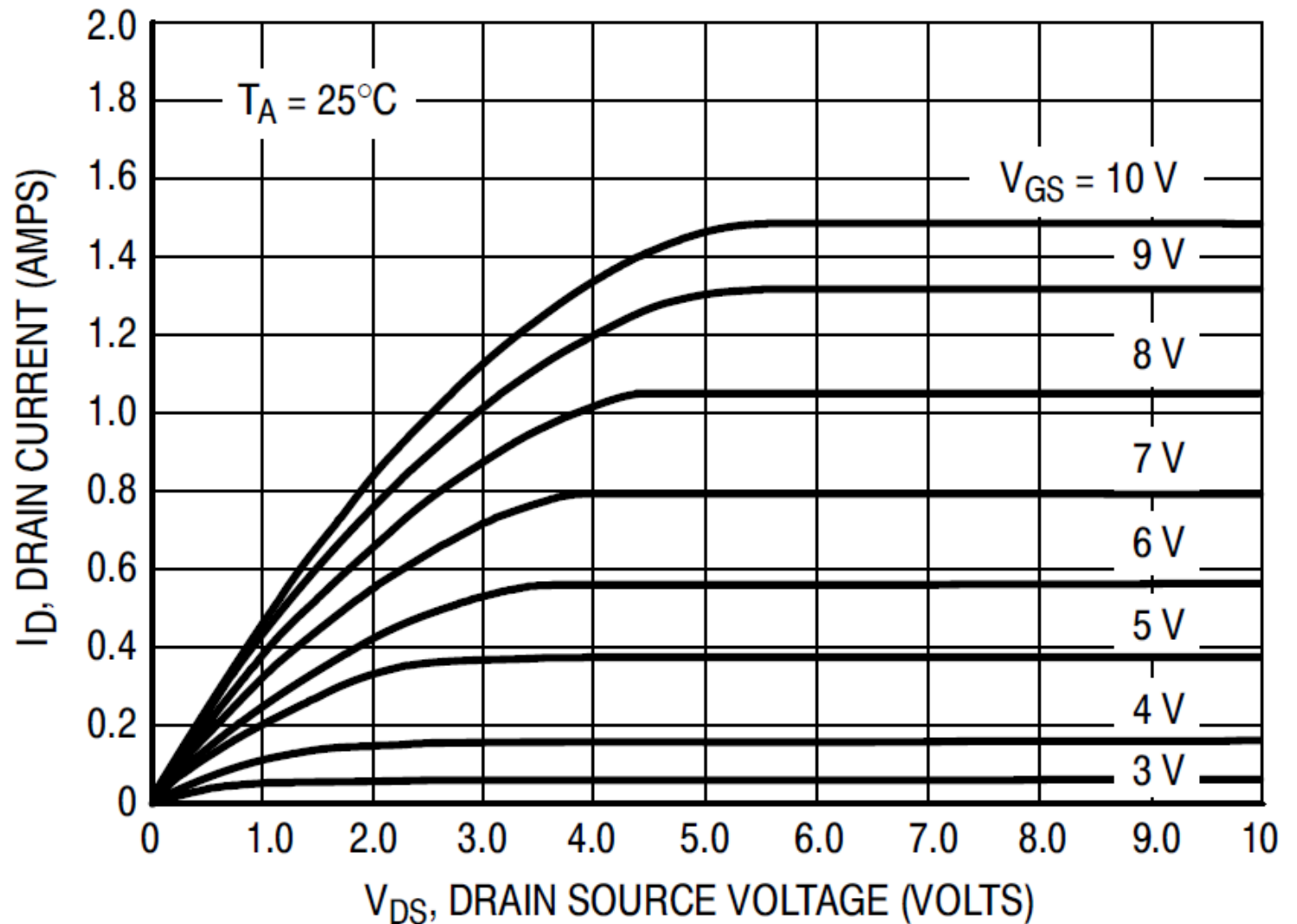
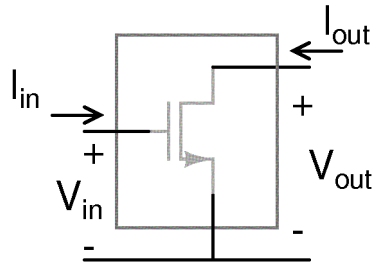
V_{GS} : 0 to 1.5V in 0.25V steps



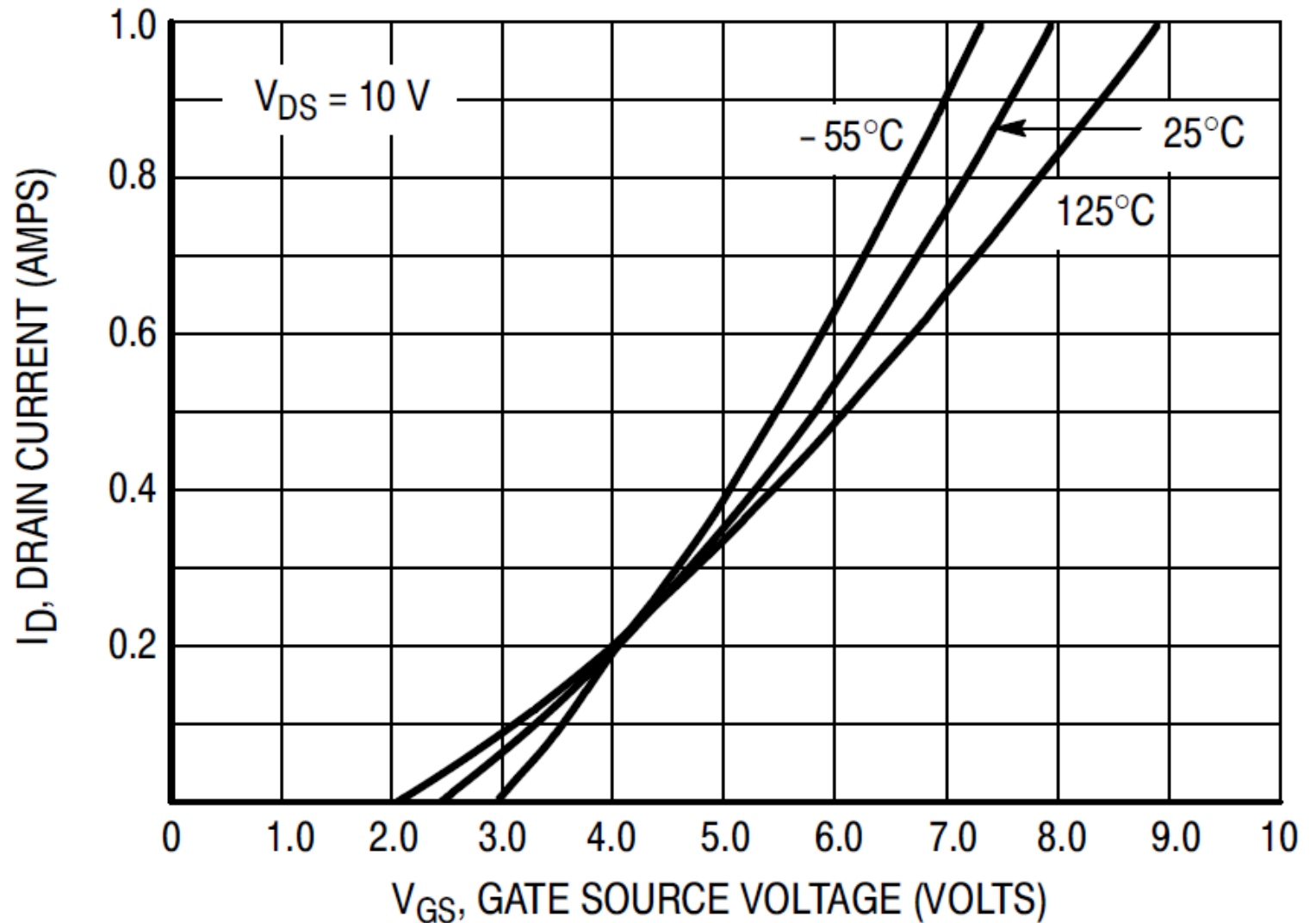
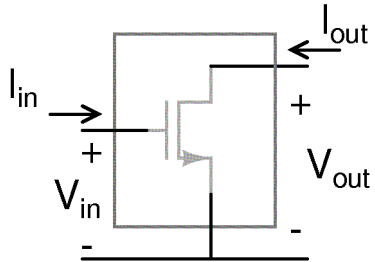
NPN: I_{out} vs. V_{out}



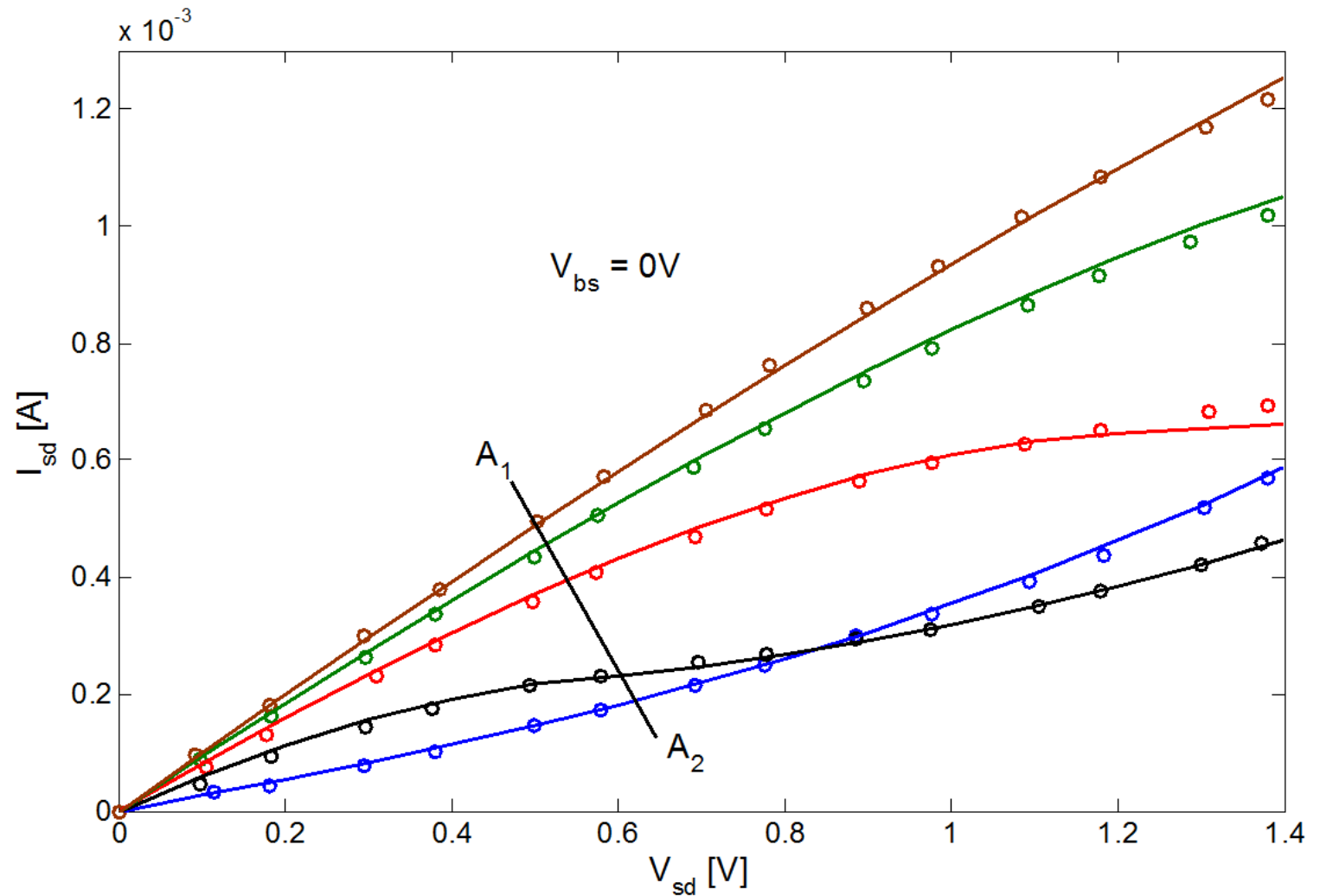
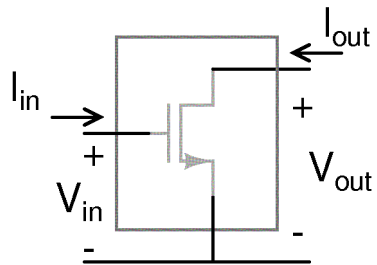
2N7000 (MOS): I_{out} vs. V_{out}



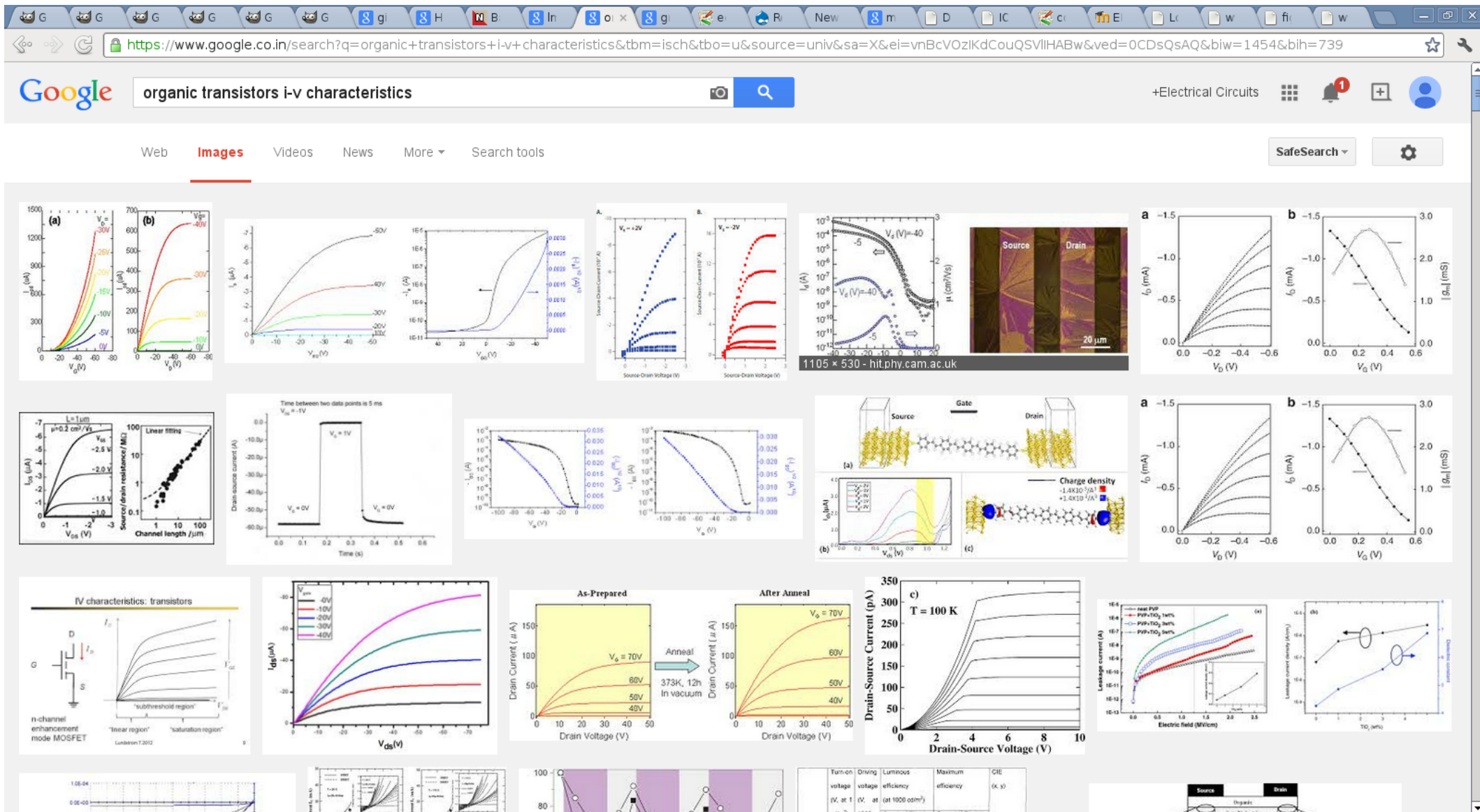
2N7000 (MOS): I_{out} vs. V_{in}



Graphene FET: I_{out} vs. V_{in}



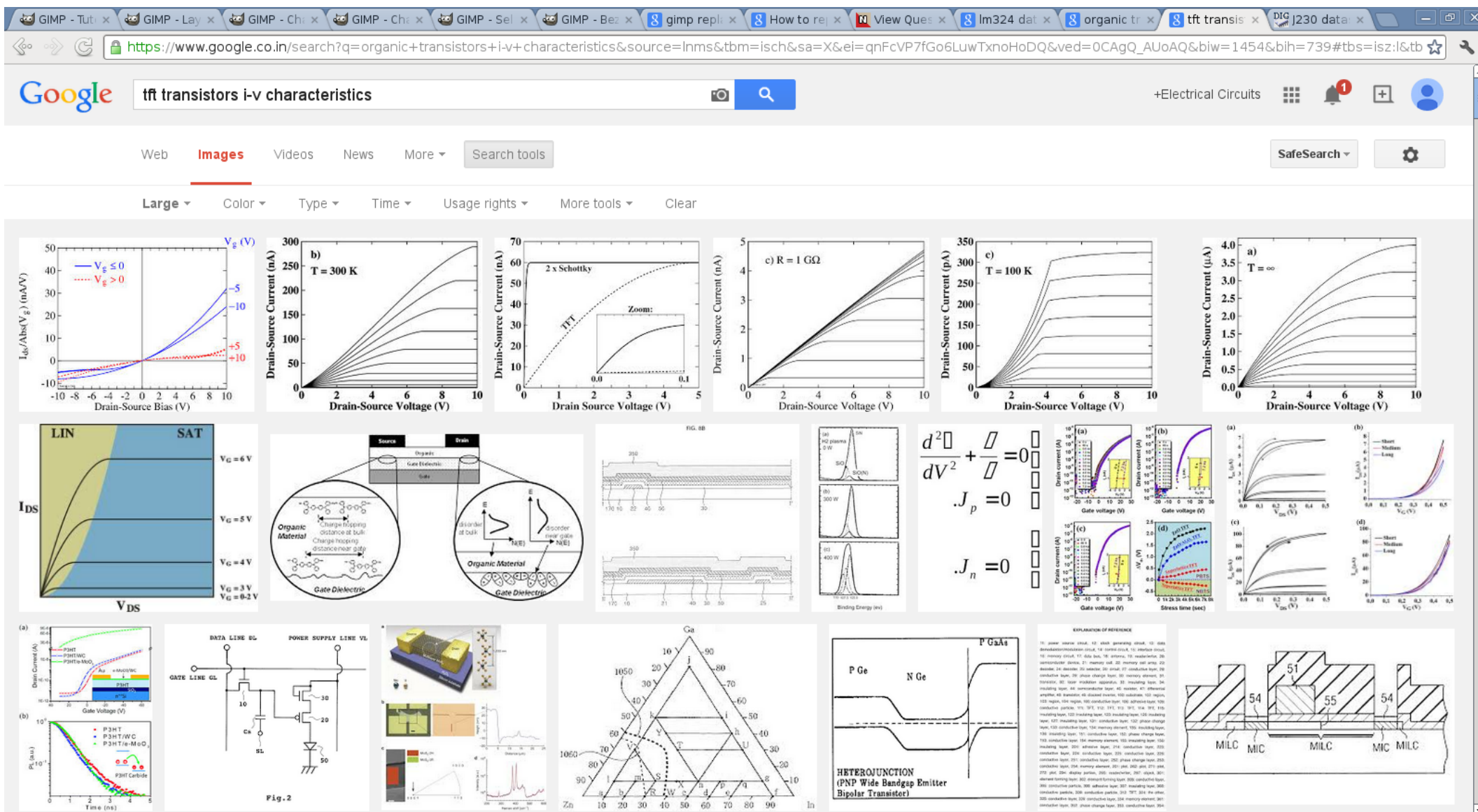
Organic transistors



Source: Google image search "organic transistors i-v characteristics"

<https://www.google.co.in/search?q=organic+transistors+i-v+characteristics&tbm=isch&tbo=u&source=univ&sa=X&ei=vnBcVOzIKdCouQSVIIHABw&ved=0CDsQsAQ&biw=1454&bih=739>

TFT transistors



Source: Google image search "tft transistor i-v characteristics" https://www.google.co.in/search?q=tft+transistor+i+v+characteristics&source=lnms&tbn=isch&sa=X&ei=EatgVJiAHIPVuQT45IKYAQ&ved=0CAgQ_AUoAQ&biw=1454&bih=739